

CFSH2-3L
SURFACE MOUNT
SILICON SCHOTTKY DIODE



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CFSH2-3L is a high quality Schottky Diode designed for applications where ultra small size and operational efficiency are prime requirements. Packaged in a Tiny Leadless Package™ (TLP™), this component provides performance characteristics suitable for the most demanding size constrained applications.

MARKING CODE: T

APPLICATIONS:

- DC / DC Converters
- Voltage Clamping
- Protection Circuits
- Battery powered devices including Cell Phones, Digital Cameras, Pagers, PDAs, Laptop Computers, etc.

FEATURES:

- $V_R=30V$
- $I_O=200mA$
- Very Low Forward Voltage Drop ($V_F=0.42V$ TYP @ 200mA)
- Reverse Current (2.5 μA TYP @ 10V)
- Small TLP™, 1mm x 0.6mm x 0.4mm, ultra low profile, Leadless Surface Mount package.

MAXIMUM RATINGS: ($T_A=25^\circ C$)

Peak Repetitive Reverse Voltage
Average Forward Current
Peak Forward Surge Current, $t_p=8.3ms$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

SYMBOL		UNITS
V_{RRM}	30	V
I_O	200	mA
I_{FSM}	3.0	A
P_D	100	mW
T_J, T_{stg}	-65 to +150	$^\circ C$
θ_{JA}	1,250	$^\circ C/W$

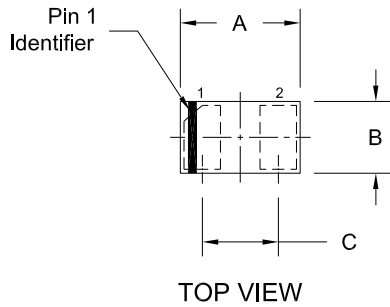
ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ C$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=10V$		4.0	10	μA
I_R	$V_R=30V$		10	50	μA
BV_R	$I_R=500\mu A$	30			V
V_F	$I_F=0.1mA$		0.115	0.19	V
V_F	$I_F=1.0mA$		0.175	0.25	V
V_F	$I_F=10mA$		0.24	0.30	V
V_F	$I_F=100mA$		0.35	0.40	V
V_F	$I_F=200mA$		0.42	0.48	V
C_T	$V_R=4.0V, f=1.0MHz$		11	25	pF

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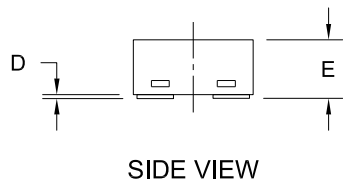


SOD-882L CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.041	0.95	1.05
B	0.022	0.026	0.55	0.65
C	0.026		0.65	
D	0.000	0.002	0.00	0.05
E	0.012	0.016	0.30	0.40
F	0.018	0.022	0.45	0.55
G	0.008	0.012	0.20	0.30

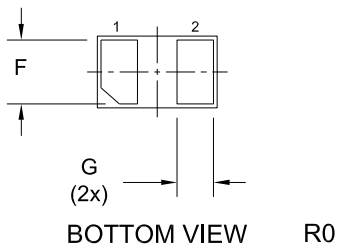
SOD-882L (REV:R0)



LEAD CODE:

- 1) Cathode
- 2) Anode

MARKING CODE: T



R2 (10-February 2011)